

Title (en)

ORGANIC SEMICONDUCTOR THIN FILM, ORGANIC THIN FILM TRANSISTOR AND METHOD FOR MANUFACTURING SAME

Title (de)

ORGANISCHE HALBLEITERDÜNN SCHICHT, ORGANISCHER DÜNN SCHICHTTRANSISTOR UND HERSTELLUNGSVERFAHREN DAFÜR

Title (fr)

FILM MINCE SEMI-CONDUCTEUR ORGANIQUE, TRANSISTOR A COUCHES MINCES ORGANIQUES ET PROCEDE DE FABRICATION DE CELUI-CI

Publication

**EP 2001063 A1 20081210 (EN)**

Application

**EP 07739052 A 20070320**

Priority

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- JP 2006082419 A 20060324

Abstract (en)

Disclosed is an organic semiconductor thin film having excellent coating property and high carrier mobility. Also disclosed are an organic thin film transistor using such an organic semiconductor thin film, and a method for manufacturing such an organic thin film transistor. Specifically disclosed is an organic semiconductor thin film formed on a base subjected to a surface treatment. This organic semiconductor thin film is characterized in that a surface treating agent used in the surface treatment has a terminal structure represented by a specific general formula.

IPC 8 full level

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CPC (source: EP US)

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Citation (search report)

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